

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 05-259250

(43)Date of publication of application : 08.10.1993

(51)Int.Cl.

H01L 21/66
 C23C 14/54
 C23C 16/50
 C23F 4/00
 G01N 21/73
 H05H 1/00
 H05H 1/46
 // H01L 21/31

(21)Application number : 04-058405

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(22)Date of filing : 16.03.1992

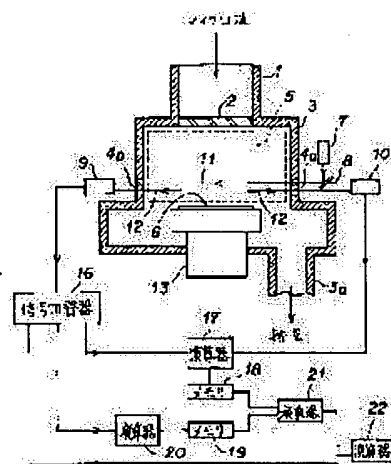
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(54) PLASMA MONITOR DEVICE OF PLASMA TREATMENT APPARATUS

(57)Abstract:

PURPOSE: To correctly monitor a plasma state in a treatment chamber and a deposit deposition state on an inner wall of the treatment chamber from outside to correctly monitor change with time in treatment characteristics in plasma treatment by knowing a change on an inner face of a light window from a spectrum distribution obtained by receiving light in a spectrometer.

CONSTITUTION: Reference light is vertically incident to a light window 4a from a reference light source 7 to be received by a spectrometer 9. An output signal containing a state of change on an inner face of light windows 4a, 4b is sent from the spectrometer 9 to an operator 20, and a spectrum distribution of the changed reference light is compared with a spectrum distribution of the reference light source 7. A wafer 6 to be treated is put into a treatment chamber 3 to generate plasma 5, the plasma is made to pass through the light windows 4a, 4b by a plasma emitting path 12 and received by spectrometers 9, 10. If the spectrum distribution of plasma emission obtained by the spectrometer 9 is corrected based on a sum and difference of internal states of the light windows 4a, 4b, light window transmission characteristics from the plasma can be correctly detected.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

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DESCRIPTION OF DRAWINGS

[Brief Description of the Drawings]

[Drawing 1] It is important section outline drawing of longitudinal section of the 1st example of this invention.

[Drawing 2] It is important section outline drawing of longitudinal section of the 2nd example of this invention.

[Drawing 3] It is important section outline drawing of longitudinal section of the 3rd example of this invention.

[Description of Notations]

2 -- microwave transparency aperture, 3 -- processing room, 4 and 4a, and 4b-- a lantern light, 5 -- plasma, 6 -- wafer, and 6 -- ' -- a mirror plane wafer, 7 -- reference source, 9, 10 -- spectroscope, and 13 -- a sample base, 14 -- half mirror, 15 -- optical fiber, and 16 -- a signal switcher, 17, 20 and 21, 22 -- computing element, 18, and 19 -- memory.

[Translation done.]

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DETAILED DESCRIPTION

[Detailed Description of the Invention]

[0001]

[Industrial Application] This invention relates to the plasma monitoring device of suitable plasma treatment equipment to carry out the monitor of the affix deposition situation of the plasma state of the processing interior of a room, and a processing indoor wall with high precision especially with respect to the processing room of plasma treatment equipment which manufactures a semiconductor device, without being influenced of a lantern light.

[0002]

[Description of the Prior Art] Highly precise micro processing is demanded with high integration of LSI. Although the engine performance of each processor of performing the processing is raised of course in order to perform highly precise processing, it is one side and it is important to maintain the engine performance of each processor to long duration stability, and not to take out a defect for a productivity drive.

[0003] In each processor, a substrate installs in the processing interior of a room of the vacuum maintenance structure where of the raw gas for etching is introduced, and if it sees about the plasma-treatment equipment which carries out plasma etching of the front face of this substrate, a resist decomposes during etching processing and the organic substance is generated, and it adheres to a processing indoor wall, or the atom of the metal (molybdenum and tungsten) this [whose] is etched material will serve as film, will adhere to a processing indoor wall, and it will accumulate. If the affix accumulated in the these processing indoor wall touches the plasma, it will generate gas by an operation of the ion in the plasma, or the temperature rise of a processing indoor wall surface, and it changes the penetration condition to the processing room of microwave by adhesion of a metal membrane. The situation of etching processing is changed with time as a result, further, the O ring for vacuum **** of a processing room deteriorates with etching gas, and generates very small leak, and the plasma state is changed.

[0004] Thus, if long duration continuous running of the etching system is carried out, aging of an etching property will occur and it will become the cause of generating of a poor product, and when the affix of a processing indoor wall becomes a certain thickness, it will separate, and it will fall and will exist as a foreign matter. It generated similarly with other plasma treatment equipments (for example, a CVD system, a sputtering system, etc.), and this phenomenon had become a failure when maintaining the engine performance of a processor to long duration stability. for this reason, the etching art which detects a specific spectrum out of plasma luminescence as that cure conventionally, carries out the monitor of the completion time of etching processing from that change on the strength, and presumes a processing property although it is necessary to monitor aging of these processing properties continuously and to predict a defect's generating in advance and the plasma -- a spectrum -- supervisory equipment (for example, JP,56-25972,A, JP,56-133466,A) is propose.

[0005]

[Problem(s) to be Solved by the Invention] In order to take out luminescence from the above-mentioned plasma from the processing interior of a room to the exterior, the aperture called a lantern light is required for the wall of a processing room, but since this lantern light is in contact with the plasma, the phenomenon in which various affixes are accumulated like the above-mentioned processing indoor wall, or a front face is deleted according to a spatter operation of the ion in the plasma accompanies. And this phenomenon advances gradually as aging also in a lantern light. In said conventional technique which takes out luminescence of the plasma to the exterior through this lantern light The phenomenon in which reflect irregularly and the quantity of light decreases is not avoided. that a specific wavelength component is absorbed by the affix accumulated in the lantern light **** -- or a lantern-light front face -- it can delete -- And since it is difficult to presume beforehand change of the spectrum distribution of plasma luminescence which considers these as a cause, it becomes difficult to detect the emission spectrum of the plasma correctly externally. For this reason, it had the trouble which cannot carry out the monitor of the affix deposition situation of the plasma state of the processing interior of a room, and a processing indoor wall correctly from the outside, and cannot carry out the monitor of the aging of the processing property in plasma treatment equipment correctly.

[0006] Moreover, although the number of equipment is the troublesome activity which requires most time amount many, for example cleaning of an affix and inspection of a surface state which were accumulated in this lantern light are conducted by disassembling equipment periodically at about several times of a rate in one month Since it was carried out in the condition that the monitor of the situation or surface state of deposition cannot be carried out correctly, the stage was too early and it also had the trouble which is too late on the contrary and loses an activity and time amount.

[0007] This invention aims at offering the plasma monitoring device in the plasma treatment equipment which can carry out the monitor of the affix deposition situation of the plasma state of the processing interior of a room, and a processing indoor wall correctly from the outside in view of the trouble of the above-mentioned conventional technique, without being influenced of a lantern light, and can carry out the monitor of the aging of the processing property in plasma treatment equipment correctly.

[0008]

[Means for Solving the Problem] The processing room in which the lantern light which this invention has vacuum

purpose was prepared, It has a means to introduce raw gas into this processing room, and the means which carries out bin/tran_web_cg generating maintenance of the plasma in this processing interior of a room. In the plasma monitoring device of the plasma treatment equipment which processes the wafer on a sample base by this plasma while carrying out the monitor of the generated plasma state The reference source in which an incidence halt is [that spectrum distribution carries out incidence of the light which has a known continuous wavelength component to a lantern light from said processing outdoor] possible, The spectroscopy which stops the reference beam and this reference beam before plasma generating from this reference source, and receives the light from the plasma after plasma generating in order the processing outdoor which passed said lantern light, A detection means to detect the lantern-light transparency property of the light from the plasma which consists of an operation means which carries out the comparison operation of each spectrum distribution of said reference beam which received light to this spectroscopy, and the light from the plasma is established.

[0009] And the spectroscopy which receives the reference beam before plasma generating which the lantern light was made to face said processing room, formed said detection means in it, and passed this each lantern light that carried out relativity, and the light from the plasma which passed one lantern light after plasma generating among said lantern lights which face processing outdoor, It is effective if it is made the configuration which prepares the spectroscopy which receives the light from the plasma which passed the lantern light of another side processing outdoor.

[0010] Moreover, the wafer on said sample base is constituted for said detection means exchangeable with a mirror plane wafer. Said lantern light is prepared in the location which faces a wafer or a mirror plane wafer, and a perpendicular. Incidence may be carried out at right angles to the mirror plane wafer on a sample base through the lantern light of this location, and you may make it the configuration which prepares the spectroscopy which receives the reference beam before plasma generating which reflected from this mirror plane wafer and passed the lantern light, and the light from the plasma which passed said lantern light after plasma generating processing outdoor.

[0011] Furthermore, said detection means is formed in the location which faces a wafer and a perpendicular in said lantern light. Incidence of the reference beam is carried out from the wafer installation side of a non-laid wafer sample base to said lantern light through the optical fiber laid underground on said sample base. And it is also possible to make it the configuration which prepares the spectroscopy which receives the reference beam before plasma generating which has the possible reference source of an incidence halt and passed said lantern light, and the light from the plasma which passed said lantern light after plasma generating processing outdoor.

[0012]

[Function] By having considered as the above-mentioned configuration, first before plasma generating under wafer conveyance etc. If spectrum distribution makes a reference beam light which has known, for example, a continuous wavelength component like the white light, from the exterior of a processing room, a lantern light is continuously introduced and passed to the processing interior of a room and a processing outdoor spectroscopy is made to receive light The wavelength component of a proper is absorbed by the matter which constitutes these affixes according to extent of are recording of the film of the organic substance with which the reference beam which passed through the processing room through this lantern light has adhered to the inside of a lantern light, or a metal membrane, and a spectrum changes. How many which wavelength components were absorbed by spectrum change of this reference beam, or the magnitude of attenuation of specific wavelength etc. is detected by it, and a class, deposited thickness of the matter which constitutes said affix are presumed. And the output signal which included the change condition of a lantern-light inside from the spectroscopy is sent to an operation means, the comparison operation of the spectrum distribution of the reference beam which this changed, and the spectrum distribution of said known reference source is carried out, and the inside condition of a lantern light is computed.

[0013] If the incidence of a reference beam is stopped next, the actually processed wafer is conveyed to the processing interior of a room, the plasma is generated, a lantern light is passed and a said processing outdoor spectroscopy is made to receive the luminescence When it can delete according to a spatter operation of the ion energy from the plasma to a lantern-light inside, ***** occurs and smoothness is lost, according to extent in which the smoothness is lost, the light from the plasma is reflected irregularly regardless of wavelength, and the quantity of light of the whole which passes a lantern light is decreased. Therefore, by detecting the decrement of the quantity of light after a predetermined period from the quantity of light in the condition that smoothness is not lost, a lantern-light inside can be deleted and extent of ***** can be known. thus, the thing for which the spectrum distribution received and acquired to said spectroscopy is a thing including the information on the change condition of a lantern-light inside, and the output signal is sent to an operation means -- a lantern-light inside -- it can delete -- etc. -- it can ask for what kind of change extent exerts on the light which passes a lantern light from the plasma.

[0014] Next, the output signal by the light from the plasma after plasma generating sent to the above-mentioned operation means and the output signal by the reference beam including the change of state of the lantern-light inside before said plasma generating calculate with this operation means, and the spectrum distribution of a reference beam is deducted from the spectrum distribution of the light from the plasma. Since this operation value becomes that in which the spectrum distribution of the light from the plasma does not include the change condition of a lantern-light inside, it becomes possible exact and to detect to arbitration, without the lantern-light transparency property of the light from the plasma being influenced by aging of a lantern light. Therefore, it becomes possible to carry out the monitor of the affix deposition situation of the plasma state of the processing interior of a room, and a processing indoor wall correctly from the outside, and to carry out the monitor of the aging of the processing property in plasma treatment equipment correctly.

[0015]

[Example] Hereafter, the example of this invention is explained with reference to drawing 1 thru/or drawing 3 . Drawing 1 is important section outline drawing of longitudinal section of the 2nd example and drawing 3 of important section outline drawing of longitudinal section of the 1st example and drawing 2] important section outline drawings of longitudinal section of the 3rd example.

[0016] The waveguide which introduces into the processing room 3 the microwave oscillated in drawing 1 from the

magnetron which 1 does not illustrate, The microwave transparency aperture by which 2 was prepared in the particular section web_cg of a waveguide 1 and the processing room 3, The raw gas the flow of [raw gas] was controlled through the quantity-of-gas-flow regulator which evacuation is carried out through exhaust pipe 3a by the evacuation system which is not illustrated, and holds the vacuum, and is not illustrated is introduced into the processing room 3, and the processing room 3 is held at the predetermined pressure. 4a and 4b are the lantern lights for taking out luminescence from the plasma to the exterior for the purpose of the spectral analysis of the plasma, are made to face the wall of the processing room 3, and are prepared. The plasma which generated 5 by microwave at the processing room 3 of a high vacuum field, the wafer with which 6 was laid on the sample base 13, and 7 are the reference sources to which spectrum distribution can irradiate the light which has known, for example, a continuous wavelength component like the white light. It is installed in the exterior of the processing room 3, and it is constituted so that the reference beam optical path 11 which carried out incidence of the reference beam at right angles to lantern-light 4a, and carried out incidence through the reflecting mirror 8 may be taken out outside through lantern-light 4b which passes through the inside of the processing room 3, and faces. The spectroscope which receives the reference beam from which 9 was taken out through lantern-light 4b outside, and 10 are spectroscopes which receive light in the exterior which passed lantern-light 4a by the plasma luminescence optical path 12 which shows luminescence of the plasma 5 generated where a reference source 7 is stopped in drawing. In this case, luminescence of the plasma 5 which made it generate where a reference source 7 is stopped is received also like a spectroscope 9, after passing lantern-light 4b by the plasma luminescence optical path 12. 16 is a signal switcher which inputs the signal of each spectrum distribution of the output signal from a spectroscope 9, i.e., the reference beam which received light, and the light from the plasma 5, and changes and outputs it to each computing elements 17, 20, and 22 according to the inputted signal. To a computing element 17, the output signal from a spectroscope 10 is also inputted into a signal and coincidence from a spectroscope 9, the difference of both spectrum distribution calculates, and it is inputted into memory 18 here. The computing element with which the computing element with which 20 calculates the difference of the known spectrum distribution of a reference source 7 and the spectrum distribution of the reference beam from said spectroscope 9, and 19 carry out memory of a computing element 20, and 21 carries out the comparison operation of the operation value of computing elements 17 and 20, and 22 are computing elements which amend the spectrum distribution of plasma luminescence obtained with said spectroscope 9 based on the operation value of a computing element 21.

[0017] In the above-mentioned configuration, processing of membrane formation of the wafer 6 laid on the sample base 13, etching, etc. introduces microwave in the direction of an illustration arrow head to the processing room 3 through a waveguide 1 and the microwave transparency aperture 2, and is performed by generating the plasma 5 for processing a wafer 6 in the processing room 3.

[0018] Incidence is carried out to a lifetime at right angles to lantern-light 4a by making into a reference beam light in which spectrum distribution has known, for example, a continuous wavelength component like the white light, from a reference source 7, and lantern-light 4b is continuously introduced and passed to it in the processing room 3, and it is made to receive light to the spectroscope 9 outside the processing room 3 the plasma of five shots under wafer 6 conveyance etc. first in processing of a wafer 6. The wavelength component of a proper is absorbed by the matter which constitutes these affixes according to extent of are recording of the film of the organic substance adhering to the inside of lantern lights 4a and 4b, or a metal membrane, and the reference beam which passed through the processing room 3 through these lantern lights 4a and 4b changes compared with the spectrum of the reference beam in the reference source 7 which does not pass lantern lights 4a and 4b. That is, the difference in this spectrum distribution supported the change of state of the inside of lantern lights 4a and 4b, and how many which wavelength components were absorbed by spectrum change of this reference beam, or the magnitude of attenuation of specific wavelength etc. is detected, and a class, deposited thickness of the matter which constitutes said affix are presumed. And the comparison operation of the difference of the spectrum distribution of a reference beam and the spectrum distribution of said known reference source 7 by which the output signal including the change condition of the aperture inside of two sheets of lantern lights 4a and 4b sent and this changed from the spectroscope 9 to the computing element 20 through the signal switcher 16 is carried out, and the result is inputted into memory 19.

[0019] Next the incidence of a reference beam is stopped, the actually processed wafer 6 is conveyed in the processing room 3, the plasma 5 is generated, lantern lights 4a and 4b are passed by the same plasma luminescence optical path 12, and the spectroscopes 9 and 10 outside said processing room 3 are made to receive the luminescence. The difference of the spectrum distribution acquired with spectroscopes 9 and 10 supports the difference in the inside condition of lantern lights 4a and 4b. When it can delete according to a spatter operation of the ion energy from the plasma 5 to lantern-light 4a and 4b inside, ***** occurs and smoothness is lost According to extent in which the smoothness is lost, the light from the plasma 5 is reflected irregularly regardless of wavelength, and the quantity of light of the whole which passes lantern lights 4a and 4b is decreased. Therefore, by detecting the decrement of the quantity of light after a predetermined period from the quantity of light in the condition that smoothness is not lost, lantern-light 4a and 4b inside can be deleted, and extent of ***** can be known. The signal of the spectrum distribution from a spectroscope 9 is put into a computing element 17 with the signal from a spectroscope 13 through the signal switcher 16, and this difference is memorized in memory 18. Even if it inputs into a computing element 21 the sum and the difference of an inside condition of lantern lights 4a and 4b which were acquired above and inside conditions differ for every information on lantern-light 4a and the inside condition of 4b each, i.e., an aperture, it can know what kind of change will be exerted on the light which passes lantern lights 4a or 4b.

[0020] If a computing element 22 amends the spectrum distribution of plasma luminescence obtained with the spectroscope 9 based on the information on above-mentioned lantern-light 4a and the inside condition of 4b each Since the spectrum distribution of the light from the plasma 5 becomes what does not include the change condition of lantern-light 4a and 4b inside, It can ask for the emission spectrum of the plasma 5, without being influenced of lantern lights 4a and 4b, and it becomes possible exact and to detect to arbitration, without the lantern-light transparency property of the light from the plasma 5 being influenced by aging of lantern lights 4a and 4b. Therefore, it becomes possible to carry out the monitor of the affix deposition situation of the plasma state in the processing room 3, and the wall of the processing room 3 correctly from the outside, and to carry out the monitor of the aging of the processing property in plasma treatment equipment correctly.

[0021] In addition, when the axial symmetry nature of the plasma 5 is good and is considered that the inside condition of lantern lights 4a and 4b is almost the same in this example, the inside condition of lantern lights 4a and 4b can be computed by making the contents of memory 19 into one half, and the contents of memory 17 become unnecessary at this time.

[0022] Below, drawing 2 explains the 2nd example of this invention. The thing of drawing 1 and a same sign shows the same thing among drawing. In drawing, 4 is the lantern light prepared for the same purpose as said 1st example, and is prepared in the location (it sets to this example and is a waveguide 1) which faces the field and perpendicular of a wafer 6 only one place. 14 is the half mirror currently installed between the reference source 7 and the lantern light 4, and introduces the reference beam from a reference source 7 at right angles to the 6th page of a wafer through a lantern light 4.

[0023] In this example, in case the wafer 6 on the sample base 13 is processed, mirror plane wafer 6' is conveyed at intervals of [fixed] the rate of one sheet etc. to 25 processing wafers at the processing room 3, and both the wafers 6 and 6' are constituted exchangeable. The total reflection light of the reference beam from the reference source 7 by which incidence was carried out at right angles to a mirror plane wafer 6'side is taken out outside through a lantern light 4 by the reference beam optical path 11 and this optical path at the time of incidence, and is reflected with a half mirror 14, and light is received with a spectroscope 9. The reflected light spectrum of a reference beam is put into a computing element 20 through the signal switcher 16 in the condition that there is almost no plasma also in this case, the one half of a difference with the spectrum distribution which does not pass the lantern light 4 of a reference source 7 is computed, and it memorizes in memory 19. This shows the effect of a lantern light 4 like said 1st example, and it becomes possible to detect the change of state of lantern-light 4 inside with time. The one half of the difference of said spectrum distribution is computed here for luminescence of the plasma 5 to which the reference beam which incidence was carried out to the mirror plane wafer 6'side, reflected in it in respect of this, and was received by the spectroscope 9 mentions a lantern light 4 later compared with passing twice passing a lantern light 4 only once.

[0024] Next, a reference beam is conveyed by the stop, the actually processed wafer 6 is conveyed on a sample base, and it processes by generating the plasma 5. Luminescence of the plasma 5 at this time is received with a spectroscope 9 through a half mirror 14. In this case, since the spectrum distribution acquired is a thing including the effect of a lantern light 4, if the value of the spectrum distribution which shows the effect of the lantern light 4 which computed using mirror plane wafer 6' and a reference beam previously, and was inputted into memory 19 is deducted with a computing element 22, the lantern-light transparency property of the light from the plasma can be detected correctly, without being influenced of a lantern light 4. Therefore, it becomes possible to carry out the monitor of the affix deposition situation of the plasma state in the processing room 3, and the wall of the processing room 3 correctly from the outside, and to carry out the monitor of the aging of the processing property in plasma treatment equipment correctly like said 1st example.

[0025] Below, drawing 3 explains the 3rd example of this invention. The thing of drawing 1, drawing 2, and a same sign shows the same thing among drawing. In drawing, the optical fiber with which 15 was laid under the sample base 13, and 15a are the tips of an optical fiber 15, and the location is the wafer 6 installation side of the sample base 13. In this example, only one place is prepared in the waveguide 1 so that it may become the location which faces the field and perpendicular of a wafer 6 like said 2nd example.

[0026] The reference beam from a reference source 7 is irradiated towards a lantern light 4 through an optical fiber 15 in the state of un-laying a wafer 6 in a condition [without the plasma] 13, i.e., sample base, top from tip 15a (location of an inferior surface of tongue of a wafer 6). A reference beam is taken out outside through a lantern light 4, and is received by the spectroscope 9 through a reflecting mirror 8. And like said 2nd example, it is put into the received reference beam by the computing element 20 through the signal switcher 16, it has a difference with the spectrum distribution which does not pass the lantern light 4 of a reference source 7 computed, and is memorized by memory 19. This shows the effect of a lantern light 4 like said 1st and 2nd example, and it becomes possible to detect the change of state of lantern-light 4 inside with time.

[0027] Next, a reference beam is conveyed by the stop, the actually processed wafer 6 is conveyed on the sample base 13, and it processes by generating the plasma 5. Luminescence of the plasma 5 at this time is received with a spectroscope 9 through a reflecting mirror 8. In this case, since the spectrum distribution acquired is a thing including the effect of a lantern light 4, if the value of the spectrum distribution which shows the effect of the lantern light 4 which computed using the reference beam previously and was inputted into memory 19 is deducted with a computing element 22, the lantern-light transparency property of the light from the plasma can be detected correctly, without being influenced of a lantern light 4. Therefore, it becomes possible to carry out the monitor of the affix deposition situation of the plasma state in the processing room 3, and the wall of the processing room 3 correctly from the outside, and to carry out the monitor of the aging of the processing property in plasma treatment equipment correctly like said 1st and 2nd example. In addition, during wafer 6 processing, in order to become the form where optical fiber tip 15a was covered with the wafer 6 and not to touch the plasma 5, even if it repeats processing, a foreign matter does not adhere to optical fiber tip 15a, or **** does not arise.

[0028] In addition, although this example explained the microwave discharge plasma, it cannot be restricted to this and can be applied similarly [in the case of the high-frequency-discharge plasma or the direct-current-discharge plasma].

[0029]

[Effect of the Invention] The effectiveness which this invention can carry out the monitor of the affix deposition situation of the plasma state of the processing interior of a room and a processing indoor wall correctly from the outside, without being influenced of a lantern light as explained above, and can carry out the monitor of the aging of the processing property in plasma treatment equipment correctly is done so.

PAT-NO: JP405259250A

DOCUMENT-IDENTIFIER: JP 05259250 A

TITLE: PLASMA MONITOR DEVICE OF PLASMA TREATMENT
APPARATUS

PUBN-DATE: October 8, 1993

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APPL-NO: JP04058405

APPL-DATE: March 16, 1992

INT-CL (IPC): H01L021/66, C23C014/54, C23C016/50, C23F004/00,
G01N021/73
, H05H001/00, H05H001/46, H01L021/31

ABSTRACT:

PURPOSE: To correctly monitor a plasma state in a treatment chamber and a deposit deposition state on an inner wall of the treatment chamber from outside to correctly monitor change with time in treatment characteristics in plasma treatment by knowing a change on an inner face of a light window from a spectrum distribution obtained by receiving light in a spectrometer.

CONSTITUTION: Reference light is vertically incident to a light window 4a from a reference light source 7 to be received by a spectrometer 9. An output signal containing a state of change on an inner face of light windows 4a, 4b is

sent from the spectrometer 9 to a operator 20, and a spectrum distribution of the changed reference light is compared with a spectrum distribution of the reference light source 7. A wafer 6 to be treated is put into a treatment chamber 3 to generate plasma 5, the plasma is made to pass through the light windows 4a, 4b by a plasma emitting path 12 and received by spectrometers 9, 10. If the spectrum distribution of plasma emission obtained by the spectrometer 9 is corrected based on a sum and difference of internal states of the light windows 4a, 4b, light window transmission characteristics from the plasma can be correctly detected.

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(19)日本国特許庁(JP)

(12) 公開特許公報(A)

(11)特許出願公開番号

特開平5-259250

(43)公開日 平成5年(1993)10月8日

(51)IntCl.⁵

識別記号

庁内整理番号

F I

技術表示箇所

H 0 1 L 21/66

P 8406-4M

C 2 3 C 14/54

8520-4K

16/50

7325-4K

C 2 3 F 4/00

A 8414-4K

G 0 1 N 21/73

9115-2J

審査請求 未請求 請求項の数4(全 8 頁) 最終頁に続く

(21)出願番号

特願平4-58405

(22)出願日

平成4年(1992)3月16日

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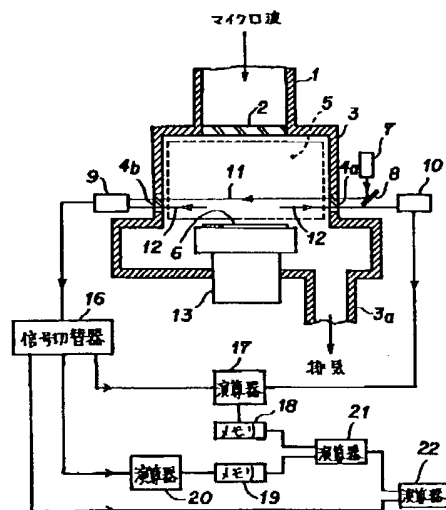
(54)【発明の名称】 プラズマ処理装置のプラズマモニタ装置

(57)【要約】 (修正有)

【目的】 処理室内のプラズマ状態および処理室内壁の付着物堆積状況を、採光窓の影響を受けることなく外部から正確にモニタし、プラズマ処理装置における処理特性の経時変化を正しくモニタすることができるプラズマ処理装置におけるプラズマモニタ装置を提供する。

【構成】 プラズマ処理装置のプラズマモニタ装置において、スペクトル分布が既知の連続的な波長成分を有する光を前記処理室外から採光窓4a、4bに垂直に入射可能な参照光源7と、該参照光源7からのプラズマ発生前の参照光および該参照光を停止しプラズマ発生後のプラズマからの光を、前記採光窓を通過した処理室外にて順に受光する分光器10と、該分光器10に受光した前記参照光およびプラズマからの光の各スペクトル分布を比較演算する演算手段20、21、22とからなるプラズマからの光の採光窓透過特性を検出する検出手段を設ける。

【図1】 本発明の第1の実施例の半部概略図



3 --- 処理室
4a, 4b --- 採光窓
5 --- プラズマ
6 --- ウェハ
7 --- 参照光源
8 --- 反射鏡
9, 10 --- 分光器
13 --- 試料台

【特許請求の範囲】

【請求項1】真空保持構造を有しプラズマからの発光を外部へ取り出す採光窓を設けた処理室と、該処理室に処理ガスを導入する手段と、該処理室内にプラズマを発生維持する手段とを有し、発生したプラズマ状態をモニタしながら該プラズマにより試料台上のウエハを処理するプラズマ処理装置のプラズマモニタ装置において、スペクトル分布が既知の連続的な波長成分を有する光を前記処理室外から採光窓に入射可能な参照光源と、該参照光源からのプラズマ発生前の参照光および該参照光を停止しプラズマ発生後のプラズマからの光を、前記採光窓を通過した処理室外にて順に受光する分光器と、該分光器に受光した前記参照光およびプラズマからの光の各スペクトル分布を比較演算する演算手段とからなるプラズマからの光の採光窓透過特性を検出する検出手段を設けたことを特徴とするプラズマ処理装置のプラズマモニタ装置。

【請求項2】前記検出手段が、前記処理室に採光窓を相対させて設け、該相対した各採光窓を通過したプラズマ発生前の参照光とプラズマ発生後に前記相対する採光窓のうち一方の採光窓を通過したプラズマからの光とを処理室外にて受光する分光器と、他方の採光窓を通過したプラズマからの光を処理室外にて受光する分光器とを設けてなる請求項1記載のプラズマ処理装置のプラズマモニタ装置。

【請求項3】前記検出手段が、前記試料台上のウエハを鏡面ウエハと交換可能に構成し、前記採光窓をウエハまたは鏡面ウエハと垂直に相対する位置に設け、該位置の採光窓を介して試料台上の鏡面ウエハに垂直に入射し、かつ該鏡面ウエハより反射して採光窓を通過したプラズマ発生前の参照光とプラズマ発生後に前記採光窓を通過したプラズマからの光とを処理室外にて受光する分光器を設けてなる請求項1記載のプラズマ処理装置のプラズマモニタ装置。

【請求項4】前記検出手段が、前記採光窓をウエハと垂直に相対する位置に設け、前記試料台上に埋設した光ファイバを介してウエハ未載置の試料台のウエハ載置面より前記採光窓に対して参照光を入射可能な参照光源を有し、前記採光窓を通過したプラズマ発生前の参照光とプラズマ発生後に前記採光窓を通過したプラズマからの光とを処理室外にて受光する分光器を設けてなる請求項1記載のプラズマ処理装置のプラズマモニタ装置。

【発明の詳細な説明】

【0001】

【産業上の利用分野】本発明は半導体デバイスを製造するプラズマ処理装置の処理室に係わり、特に処理室内のプラズマ状態及び処理室内壁の付着物堆積状況を、採光窓の影響を受けることなく高精度にモニタするのに好適なプラズマ処理装置のプラズマモニタ装置に関する。

【0002】

【従来の技術】LSIの高集積化に伴い、高精度の微細加工が要求されている。高精度の加工を行うためには、その加工を行う各処理装置の性能を向上させることはもちろんであるが、一方で、生産性向上のために各処理装置の性能を長時間安定に維持して不良を出さないことが重要である。

【0003】各処理装置の中で、エッチング用処理ガスが導入される真空保持構造の処理室内に基板を設置し、該基板の表面をプラズマエッチングするプラズマ処理装置についてみると、エッチング処理中にレジストが分解して有機物が発生し、これが処理室内壁に付着したり、或いは、被エッチング材である金属（モリブデンやタンゲステン）の原子が処理室内壁に膜となって付着したりして蓄積する。これら処理室内壁に蓄積した付着物は、プラズマに接するとプラズマ中のイオンの作用や処理室内壁面の温度上昇によりガスを発生したり、また、金属膜の付着によりマイクロ波の処理室への進入状態を変化させたりして、結果的にエッチング処理の状況を経時的に変化させ、さらに、処理室の真空封じのためのリングが、エッチングガスにより劣化して微少なリークを発生しプラズマ状態を変化させたりする。

【0004】このように、エッチング装置を長時間連続運転していると、エッチング特性の経時変化が起きて製品不良の発生原因となり、また、処理室内壁の付着物は、ある厚みになると剥がれ落ちて異物として存在することになる。この現象は、他のプラズマ処理装置（例えば、CVD装置やスパッタ装置等）でも同様に発生し、処理装置の性能を長時間安定に維持する上で障害となっていた。このため、これらの処理特性の経時変化を常時監視し、不良の発生を事前に予測することが必要になるが、従来はその対策として、プラズマ発光の中から特定のスペクトルを検出し、その強度変化からエッチング処理の完了時点をモニタして処理特性を推定するエッチング処理方法やプラズマ分光監視装置（例えば、特開昭56-25972号公報、特開昭56-133466号公報）が提案されている。

【0005】

【発明が解決しようとする課題】上記プラズマからの発光を処理室内から外部へ取り出すためには、処理室の壁に採光窓と呼ぶ窓が必要であるが、この採光窓は、プラズマに接しているために前述の処理室内壁と同様に種々の付着物が蓄積したり、プラズマ中のイオンのスパッタ作用により表面が削られたりする現象が付随する。そして、この現象は採光窓においても経時変化として徐々に進行する。かかる採光窓を通してプラズマの発光を外部へ取り出す前記従来技術においては、採光窓に蓄積した付着物により特定の波長成分が吸収されたり、或いは採光窓表面の削れにより乱反射して光量が減少する現象が避けられず、しかも、これらを原因とするプラズマ発光のスペクトル分布の変化をあらかじめ推定することが困難

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難であることから、プラズマの発光スペクトルを外部で正確に検出することが困難になる。このため、処理室内のプラズマ状態および処理室内壁の付着物堆積状況を外部から正確にモニタすることができず、プラズマ処理装置における処理特性の経時変化を正しくモニタすることができない問題点を有していた。

【0006】また、この採光窓に蓄積した付着物の清掃や表面状態の検査は、装置数が多くかなりの時間を要する煩わしい作業であるにもかかわらず、例えば一ヶ月に数回程度の割合で定期的に装置を分解して行われるが、堆積の状況や表面状態を正確にモニタできない状態で行われるため、時期が早すぎたり、反対に遅すぎたりして作業および時間をロスする問題点も有していた。

【0007】本発明は、上記従来技術の問題点に鑑み、処理室内のプラズマ状態および処理室内壁の付着物堆積状況を、採光窓の影響を受けることなく外部から正確にモニタし、プラズマ処理装置における処理特性の経時変化を正しくモニタすることができるプラズマ処理装置におけるプラズマモニタ装置を提供することを目的とする。

【0008】

【課題を解決するための手段】上記目的を達成するため、本発明は、真空保持構造を有しプラズマからの発光を外部へ取り出す採光窓を設けた処理室と、該処理室に処理ガスを導入する手段と、該処理室内にプラズマを発生維持する手段とを有し、発生したプラズマ状態をモニタしながら該プラズマにより試料台上のウエハを処理するプラズマ処理装置のプラズマモニタ装置において、スペクトル分布が既知の連続的な波長成分を有する光を前記処理室外から採光窓に入射し、かつ入射停止の可能な参照光源と、該参照光源からのプラズマ発生前の参照光および該参照光を停止しプラズマ発生後のプラズマからの光を、前記採光窓を通過した処理室外にて順に受光する分光器と、該分光器に受光した前記参照光およびプラズマからの光の各スペクトル分布を比較演算する演算手段とからなるプラズマからの光の採光窓透過特性を検出する検出手段を設けるようにしたものである。

【0009】そして、前記検出手段を、前記処理室に採光窓を相対させて設け、該相対した各採光窓を通過したプラズマ発生前の参照光とプラズマ発生後に前記相対する採光窓のうち一方の採光窓を通過したプラズマからの光とを処理室外にて受光する分光器と、他方の採光窓を通過したプラズマからの光を処理室外にて受光する分光器とを設ける構成にすると効果的である。

【0010】また、前記検出手段を、前記試料台上のウエハを鏡面ウエハと交換可能に構成し、前記採光窓をウエハまたは鏡面ウエハと垂直に相対する位置に設け、該位置の採光窓を介して試料台上の鏡面ウエハに垂直に入射し、かつ該鏡面ウエハより反射して採光窓を通過したプラズマ発生前の参照光とプラズマ発生後に前記採光窓

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を通過したプラズマからの光とを処理室外にて受光する分光器を設ける構成にしてもよい。

【0011】さらに、前記検出手段を、前記採光窓をウエハと垂直に相対する位置に設け、前記試料台上に埋設した光ファイバを介してウエハ未載置の試料台のウエハ載置面より前記採光窓に対して参照光を入射し、かつ入射停止の可能な参照光源を有し、前記採光窓を通過したプラズマ発生前の参照光とプラズマ発生後に前記採光窓を通過したプラズマからの光とを処理室外にて受光する分光器を設ける構成にすることも可能である。

【0012】

【作用】上記構成としたことにより、まず、ウエハ搬送中などのプラズマ発生前に、処理室の外部からスペクトル分布が既知の、例えば白色光のような連続的な波長成分を有する光を参照光として処理室内に導入し、ついで採光窓を通過して処理室外の分光器に受光させると、この採光窓を介して処理室を通過した参照光は、採光窓の内面に付着している有機物の膜や金属膜の蓄積の程度に応じて、それら付着物を構成している物質に固有の波長成分が吸収され、スペクトルが変化する。この参照光のスペクトル変化により、どの波長成分がどの程度吸収されたか、或いは特定の波長の減衰量等が検出され、前記付着物を構成している物質の種類や堆積している厚さなどが推定される。そして、分光器から採光窓内面の変化状態を含んだ出力信号が演算手段に送られ、該変化した参照光のスペクトル分布と前記既知の参照光源のスペクトル分布とが比較演算され、採光窓の内面状態が算出される。

【0013】つぎに参照光の入射を停止し、実際に処理するウエハを処理室内に搬送してプラズマを発生させ、その発光を採光窓を通過させて前記処理室外の分光器に受光させると、採光窓内面にプラズマからのイオンエネルギーのスパッタ作用により削れや荒れが発生して平滑度が失われている場合は、その平滑度が失われている程度に応じてプラズマからの光を波長に無関係に乱反射し、採光窓を通過する全体の光量を減少させる。そのため、平滑度が失われていない状態の光量から所定期間後の光量の減少量を検出することにより採光窓内面の削れや荒れの程度を知ることができる。このように前記分光器に受光して得たスペクトル分布は、採光窓内面の変化状態の情報を含んだものになっており、その出力信号が演算手段に送られることにより、採光窓内面の削れ等の程度が採光窓を通過するプラズマからの光にどのような変化を及ぼすかを求めることができる。

【0014】つぎに、上記演算手段に送られたプラズマ発生後のプラズマからの光による出力信号と、前記プラズマ発生前の採光窓内面の状態変化を含んだ参照光による出力信号とが該演算手段により演算され、プラズマからの光のスペクトル分布から参照光のスペクトル分布が差し引かれる。この演算値は、プラズマからの光のスペ

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クトル分布が採光窓内面の変化状態を含まないものになるため、プラズマからの光の採光窓透過特性を採光窓の経時変化に影響されことなく正確かつ任意に検出することが可能になる。従って、処理室内のプラズマ状態および処理室内壁の付着物堆積状況を外部から正確にモニタし、プラズマ処理装置における処理特性の経時変化を正しくモニタすることが可能になる。

【0015】

【実施例】以下、本発明の実施例を図1ないし図3を参照して説明する。図1は第1の実施例の要部概略縦断面図、図2は第2の実施例の要部概略縦断面図、図3は第3の実施例の要部概略縦断面図である。

【0016】図1において、1は図示しないマグネトロンから発振されたマイクロ波を処理室3に導入する導波管、2は導波管1と処理室3との仕切り部に設けられたマイクロ波透過窓、処理室3は図示しない真空排気系により排気管3aを通じて真空排気されて真空を保持しており、かつ図示していないガス流量調整器を通じて流量調整された処理ガスが処理室3に導入され所定の圧力に保持されている。4a、4bはプラズマの分光分析を目的としてプラズマからの発光を外部へ取り出すための採光窓で、処理室3の壁に相対させて設けられている。5は高真空領域の処理室3でマイクロ波によって発生したプラズマ、6は試料台13上に載置されたウエハ、7はスペクトル分布が既知の、例えば白色光のような連続的な波長成分を有する光を照射可能な参照光源で、処理室3の外部に設置され、参照光を反射鏡8を介して採光窓4aに垂直に入射し、入射した参照光光路11が処理室3内を通過して相対する採光窓4bを経て外部へ取り出されるように構成されている。9は採光窓4bを経て外部へ取り出された参照光を受光する分光器、10は参照光源7を停止した状態で発生させたプラズマ5の発光を、図に示すプラズマ発光光路12で採光窓4aを通過させた外部で受光する分光器である。この場合、参照光源7を停止した状態で発生させたプラズマ5の発光は、プラズマ発光光路12で採光窓4bを通過させた後、分光器9にも同様に受光される。16は分光器9からの出力信号、すなわち受光した参照光およびプラズマ5からの光の各スペクトル分布の信号を入力し、入力した信号に応じて各演算器17、20、22に切り替えて出力する信号切替器である。ここで演算器17には、分光器9からの信号と同時に分光器10からの出力信号も入力され、両者のスペクトル分布の差が演算されてメモリ18に入力される。20は参照光源7の既知のスペクトル分布と前記分光器9からの参照光のスペクトル分布の差を演算する演算器、19は演算器20のメモリ、21は演算器17および20の演算値を比較演算する演算器、22は演算器21の演算値をもとに前記分光器9にて得たプラズマ発光のスペクトル分布を補正する演算器である。

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【0017】上記構成において、試料台13上に載置されたウエハ6の成膜やエッチング等の処理は、マイクロ波を図示矢印方向に導波管1およびマイクロ波透過窓2を経て処理室3へ導入し、処理室3内にウエハ6を処理するためのプラズマ5を発生させて行われる。

【0018】ウエハ6の処理に当たって、まず、ウエハ6搬送中などのプラズマ5発生前に、参照光源7からスペクトル分布が既知の、例えば白色光のような連続的な波長成分を有する光を参照光として採光窓4aに垂直に入射して処理室3内に導入し、つづいて採光窓4bを通過して処理室3外の分光器9に受光させる。この採光窓4a、4bを介して処理室3を通過した参照光は、採光窓4a、4bの内面に付着している有機物の膜や金属膜の蓄積の程度に応じて、それら付着物を構成している物質に固有の波長成分が吸収され、採光窓4a、4bを通過しない参照光源7における参照光のスペクトルに比べて変化する。すなわち、このスペクトル分布の違いは採光窓4a、4bの内面の状態変化に対応しており、この参照光のスペクトル変化により、どの波長成分がどの程度吸収されたか、或いは特定の波長の減衰量等が検出され、前記付着物を構成している物質の種類や堆積している厚さなどが推定される。そして、分光器9から採光窓4a、4bの2枚の窓内面の変化状態を含んだ出力信号が信号切替器16を経て演算器20に送られ、該変化した参照光のスペクトル分布と前記既知の参照光源7のスペクトル分布との差が比較演算され、その結果がメモリ19に入力される。

【0019】つぎに参照光の入射を停止し、実際に処理するウエハ6を処理室3内に搬送してプラズマ5を発生させ、その発光を同一のプラズマ発光光路12で採光窓4a、4bを通過させて前記処理室3外の分光器9および10に受光させる。分光器9、10で得たスペクトル分布の差は採光窓4a、4bの内面状態の違いに対応しており、採光窓4a、4b内面にプラズマ5からのイオンエネルギーのスパッタ作用により削れや荒れが発生して平滑度が失われている場合は、その平滑度が失われている程度に応じてプラズマ5からの光を波長に無関係に乱反射し、採光窓4a、4bを通過する全体の光量を減少させる。そのため、平滑度が失われていない状態の光量から所定期間後の光量の減少量を検出することにより採光窓4a、4b内面の削れや荒れの程度を知ることができる。分光器9からのスペクトル分布の信号を信号切替器16を経て分光器13からの信号と共に演算器17に入れ、この差をメモリ18に記憶しておく。以上で得た採光窓4a、4bの内面状態の和および差を演算器21に入力し、採光窓4a、4b個々の内面状態の情報、すなわち、窓ごとに内面状態が異なっている、採光窓4aまたは4bを通過する光にどのような変化を及ぼすかを知ることができる。

50 【0020】上記採光窓4a、4b個々の内面状態の情

報をもとに、分光器9で得たプラズマ発光のスペクトル分布を演算器22で補正すれば、プラズマ5からの光のスペクトル分布が採光窓4a、4b内面の変化状態を含まないものになるため、プラズマ5の発光スペクトルを採光窓4a、4bの影響を受けることなく求めることができ、プラズマ5からの光の採光窓透過特性を採光窓4a、4bの経時変化に影響されことなく正確かつ任意に検出することが可能になる。従って、処理室3内のプラズマ状態および処理室3の内壁の付着物堆積状況を外部から正確にモニタし、プラズマ処理装置における処理特性の経時変化を正しくモニタすることが可能になる。

【0021】なお、本実施例においてプラズマ5の軸対称性がよく、採光窓4aと4bの内面状態がほぼ同じと考えられる場合には、メモリ19の内容を半分にするだけで採光窓4a、4bの内面状態が算出でき、このときメモリ17の内容は不要になる。

【0022】つぎに、本発明の第2の実施例を図2により説明する。図中、図1と同符号のものは同じものを示す。図において、4は前記第1の実施例と同一の目的で設けられた採光窓で、ウエハ6の面と垂直に相対する位置（本実施例においては導波管1）に1個所だけ設けられている。14は参照光源7と採光窓4との間に設置されているハーフミラーで、参照光源7からの参照光を採光窓4を介してウエハ6面に垂直に導入するようになっている。

【0023】本実施例においては、試料台13上のウエハ6を処理する際に、例えば、処理ウエハ25枚に1枚の割合等の一定間隔で鏡面ウエハ6⁺を処理室3に搬送し、両ウエハ6、6⁻を交換可能に構成している。鏡面ウエハ6⁺面に垂直に入射された参照光源7からの参照光の全反射光を、入射時の参照光光路11と同光路で採光窓4を介して外部に取り出し、ハーフミラー14により反射させ分光器9で受光する。この場合も、まずプラズマの無い状態で参照光の反射光スペクトルを信号切替器16を経て演算器20に入れ、参照光源7の採光窓4を通過しないスペクトル分布との差の半分を算出しメモリ19に記憶する。これは前記第1の実施例と同様に採光窓4の影響を示すもので、採光窓4内面の状態変化を経時的に検出することが可能になる。ここで前記スペクトル分布の差の半分を算出するのは、鏡面ウエハ6⁺面に入射され該面に反射して分光器9に受光された参照光が、採光窓4を2回通過するのに比べて、後述するプラズマ5の発光が採光窓4を1回しか通過しないためである。

【0024】つぎに参照光を止め、実際に処理するウエハ6を試料台上に搬送し、プラズマ5を発生させ処理を行う。このときのプラズマ5の発光をハーフミラー14を経て分光器9で受光する。この場合に得られるスペクトル分布は、採光窓4の影響を含んだものとなっているので、先に鏡面ウエハ6⁺と参照光を用いて算出しメモ

リ19に入力した採光窓4の影響を示すスペクトル分布の値を演算器22により差し引けば、採光窓4の影響を受けることなくプラズマからの光の採光窓透過特性を正確に検出することができる。従って前記第1の実施例と同様に、処理室3内のプラズマ状態および処理室3の内壁の付着物堆積状況を外部から正確にモニタし、プラズマ処理装置における処理特性の経時変化を正しくモニタすることが可能になる。

【0025】つぎに、本発明の第3の実施例を図3により説明する。図中、図1、図2と同符号のものは同じものを示す。図において、15は試料台13に埋設された光ファイバ、15aは光ファイバ15の先端で、その位置は試料台13のウエハ6載置面である。本実施例では前記第2の実施例と同様に、ウエハ6の面と垂直に相対する位置になるように導波管1に1個所だけ設けられている。

【0026】プラズマの無い状態、つまり試料台13上にウエハ6が未載置の状態で、参照光源7からの参照光が光ファイバ15を介してその先端15a（ウエハ6の下面相当の位置）から採光窓4に向けて照射される。参照光は採光窓4を経て外部に取り出され、反射鏡8を介して分光器9に受光される。そして前記第2の実施例と同様に、受光された参照光は信号切替器16を経て演算器20に入れられ、参照光源7の採光窓4を通過しないスペクトル分布との差を算出されてメモリ19に記憶される。これは前記第1、第2の実施例と同様に採光窓4の影響を示すもので、採光窓4内面の状態変化を経時的に検出することが可能になる。

【0027】つぎに参照光を止め、実際に処理するウエハ6を試料台13上に搬送し、プラズマ5を発生させ処理を行う。このときのプラズマ5の発光を反射鏡8を経て分光器9で受光する。この場合に得られるスペクトル分布は、採光窓4の影響を含んだものとなっているので、先に参照光を用いて算出しメモリ19に入力した採光窓4の影響を示すスペクトル分布の値を演算器22により差し引けば、採光窓4の影響を受けることなくプラズマからの光の採光窓透過特性を正確に検出することができる。従って前記第1、第2の実施例と同様に、処理室3内のプラズマ状態および処理室3の内壁の付着物堆積状況を外部から正確にモニタし、プラズマ処理装置における処理特性の経時変化を正しくモニタすることが可能になる。なお、ウエハ6処理中は、光ファイバ先端15aがウエハ6に覆われた形になりプラズマ5に接しないため、処理を繰り返しても光ファイバ先端15aに異物が付着したり削れが生じたりすることはない。

【0028】なお、本実施例はマイクロ波放電プラズマについて説明したが、これに限るものではなく、高周波放電プラズマや直流放電プラズマの場合にも同様に適用することができる。

【0029】

【発明の効果】以上説明したように本発明は、処理室内のプラズマ状態および処理室内壁の付着物堆積状況を、採光窓の影響を受けることなく外部から正確にモニタし、プラズマ処理装置における処理特性の経時変化を正しくモニタすることができる効果を奏する。

【図面の簡単な説明】

【図1】本発明の第1の実施例の要部概略縦断面図である。

【図2】本発明の第2の実施例の要部概略縦断面図である。

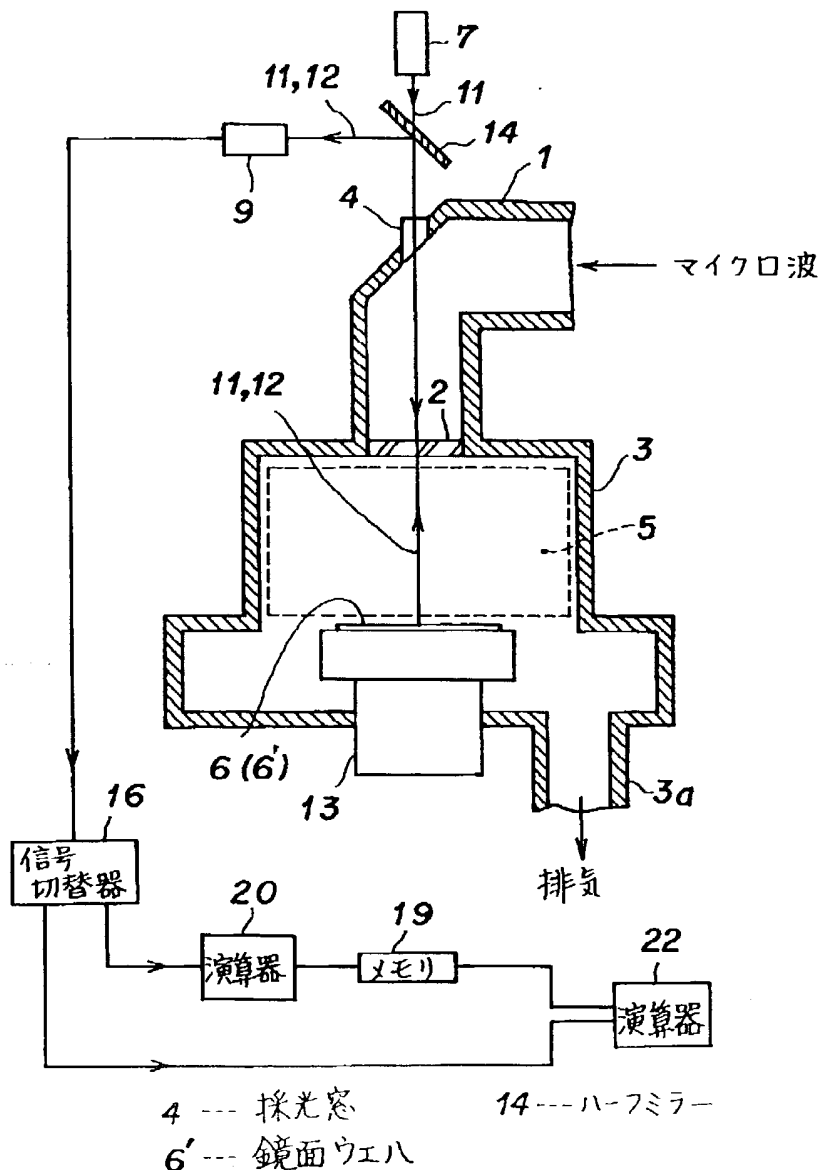
【図3】本発明の第3の実施例の要部概略縦断面図である。

【符号の説明】

2…マイクロ波透過窓、3…処理室、4, 4a, 4b…採光窓、5…プラズマ、6…ウェハ、6'…鏡面ウェハ、7…参照光源、9, 10…分光器、13…試料台、14…ハーフミラー、15…光ファイバ、16…信号切替器、17, 20, 21, 22…演算器、18, 19…メモリ。

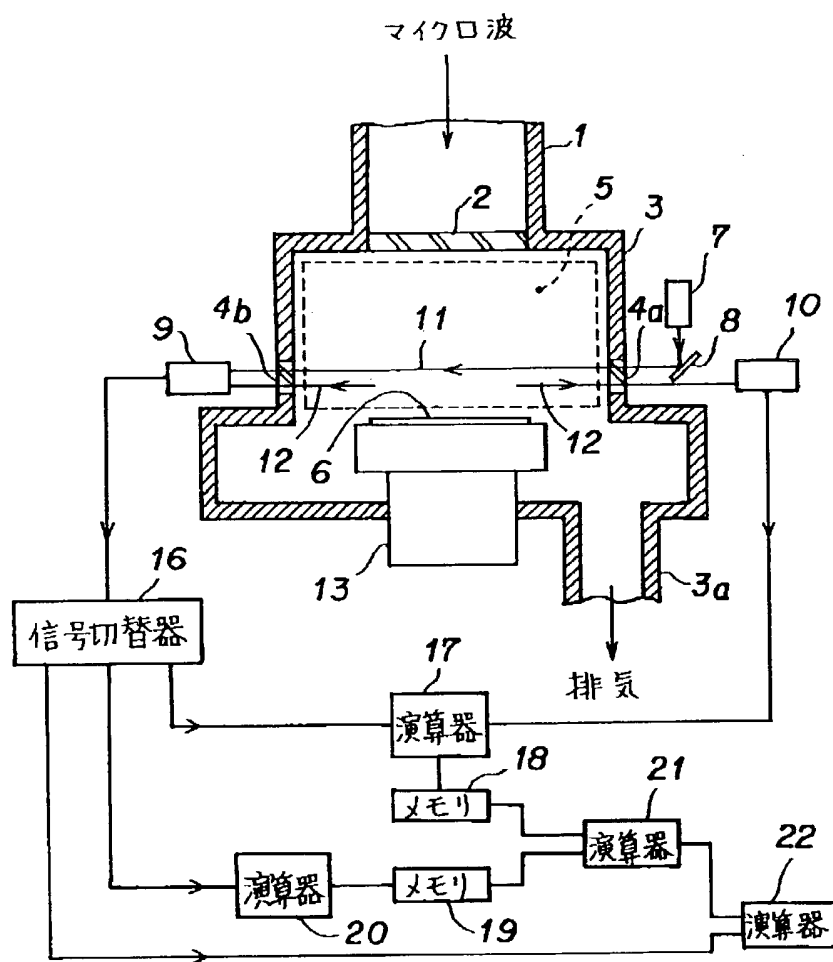
【図2】

【図2】本発明の第2の実施例の要部概略図



【図1】

【図1】 本発明の第1の実施例の要部概略図



3 --- 処理室

7 --- 参照光源

4a, 4b --- 採光窓

8 --- 反射鏡

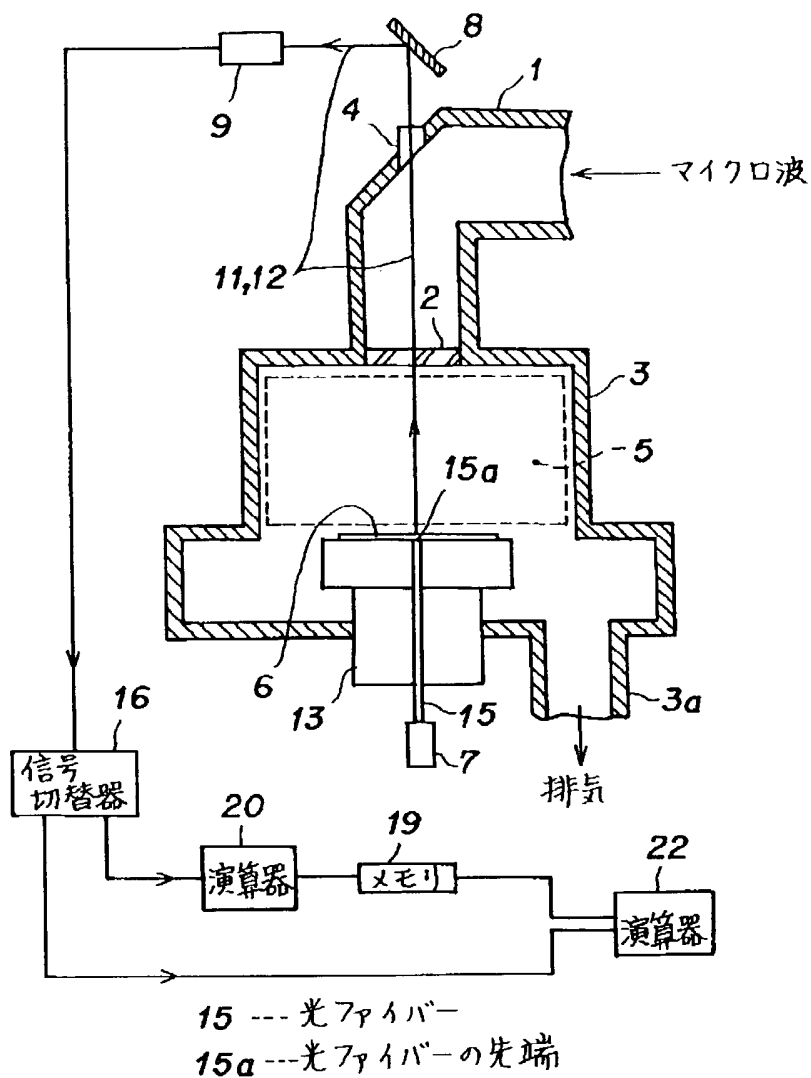
5 --- プラズマ

9, 10 --- 分光器

6 --- ウエハ

13 --- 試料台

【図 3】 本発明の第3の実施例の要部概略図



(51) Int. Cl. ⁵

識別記号

片内整理番号

FI

技術表示箇所

Z 8406-4M

A 9014-2G

9014-2G

C